

PHP225

Dual P-channel intermediate level FET Rev. 04 — 17 March 2011

Product data sheet

Product profile 1.

1.1 General description

Dual intermediate level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using vertical D-MOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- Motor and actuator drivers
- Power management

Synchronized rectification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	-30	V
I _D	drain current	T _{sp} ≤ 80 °C		-	-	-2.3	Α
P _{tot}	total power dissipation	T _{sp} = 80 °C	[1]	-	-	2	W
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V; } I_D = -1 \text{ A;}$ $T_j = 25 \text{ °C}$		-	0.22	0.25	Ω
Dynamic c	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = -10 \text{ V}; I_D = -2.3 \text{ A};$ $V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$		-	3	-	nC

^[1] Maximum permissible dissipation per MOS transistor. Both devices may be loaded up to 2 W at the same



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		B4 B4 B5 B5
2	G1	gate1	8 <u>P P P P</u> 5	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1	S1 G1 S2 G2
6	D2	drain2	SOT96-1 (SO8)	sym115
7	D1	drain1		
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP225	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$		-	-30	V
V_{GS}	gate-source voltage			-	-	V
V_{GSO}	gate-source voltage	open drain		-20	20	V
I_{D}	drain current	T _{sp} ≤ 80 °C		-	-2.3	Α
I _{DM}	peak drain current	T _{sp} = 25 °C; pulsed	<u>[1]</u>	-	-10	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	1	W
		T _{sp} = 80 °C	<u>[3]</u>	-	2	W
		T _{amb} = 25 °C	<u>[4]</u>	-	1.3	W
			<u>[5]</u>	-	2	W
T _{stg}	storage temperature			-65	150	°C
Tj	junction temperature			-	150	°C
Source-drain	diode					
Is	source current	T _{sp} ≤ 80 °C		-	-1.25	Α
I _{SM}	peak source current	T _{sp} = 25 °C; pulsed	<u>[1]</u>	-	-5	Α

^[1] Pulse width and duty cycle limited by maximum junction temperature.

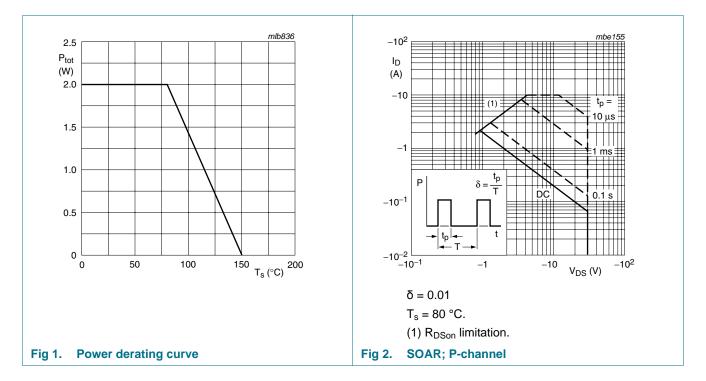
^[2] Maximum permissible dissipation per MOS transistor. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 90 K/W.

^[3] Maximum permissible dissipation per MOS transistor. Both devices may be loaded up to 2 W at the same time.

^[4] Maximum permissible dissipation if only one MOS transistor dissipates. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 90 K/W.

^[5] Maximum permissible dissipation per MOS transistor. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 27.5 K/W.

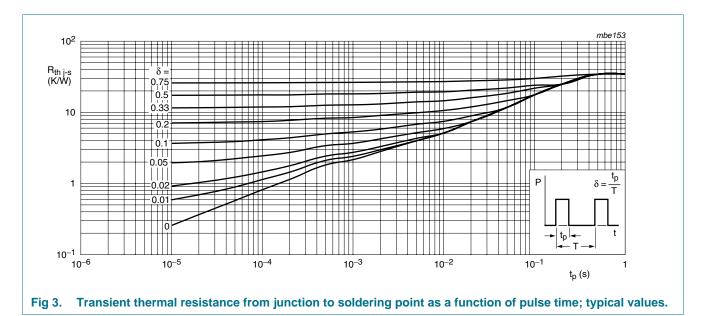
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 3	-	-	35	K/W



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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1	-	-2.8	V
I _{DSS}	drain leakage current	$V_{DS} = -24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
I _{GSS} gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ	
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon} drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -1 \text{ A}; T_j = 25 \text{ °C}$	-	0.22	0.25	Ω	
	$V_{GS} = -4.5 \text{ V}; I_D = -0.5 \text{ A}; T_j = 25 \text{ °C}$	-	0.33	0.4	Ω	
I _{DSon} on-state drain current	on-state drain current	$V_{DS} = -1 \ V; \ V_{GS} = -10 \ V$	-2.3	-	-	Α
		$V_{DS} = -5 \text{ V}; V_{GS} = -4.5 \text{ V}$	-1	-	-	Α
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = -2.3 \text{ A}; V_{DS} = -15 \text{ V}; V_{GS} = -10 \text{ V};$	-	10	25	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	3	-	nC
C _{iss}	input capacitance	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	250	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	140	-	pF
C _{rss}	reverse transfer capacitance		-	50	-	pF
g _{fs}	transfer conductance	$V_{DS} = -20 \text{ V}; I_D = -1 \text{ A}; T_j = 25 \text{ °C}$	1	2	-	S
t _{off}	turn-off time	V_{DS} = -20 V; V_{GS} = -10 V; $R_{G(ext)}$ = 4.7 Ω ;	-	50	140	ns
t _{on}	turn-on time	$R_L = 20 \Omega; T_j = 25 °C; I_D = -1 A$	-	20	80	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -1.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1.6	V
t _{rr}	reverse recovery time	$I_S = -1.25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 25 \text{ V}$; $T_1 = 25 \text{ °C}$	-	150	200	ns

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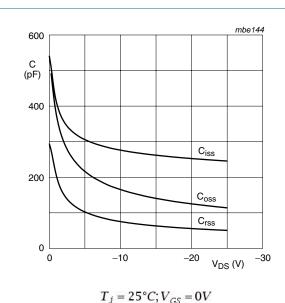
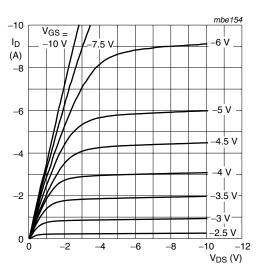


Fig 4. Capacitance as a function of drain-source voltage; P-channel; typical values



$$T_j = 25^{\circ}C$$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; P-channel; typical values

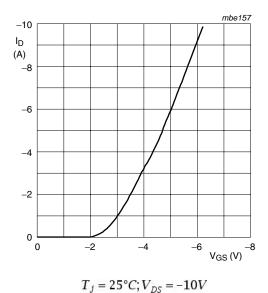
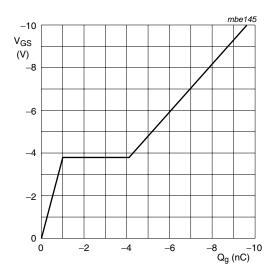


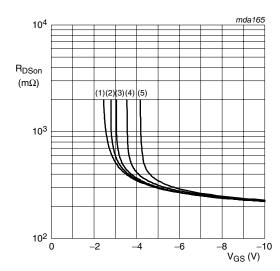
Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; P-channel; typical values



$$I_D = -2.3A; V_{DS} = -15V$$

Fig 7. Gate-source voltage as a function of gate charge; P-channel; typical values

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 $-V_{DS} \ge -I_D \times R_{DSon}$; $T_j = 25 \, ^{\circ}C$.

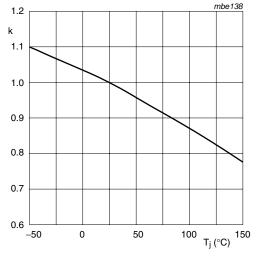
(1)
$$I_D = -0.1 A$$
.

(2)
$$I_D = -0.5 A$$
.

(3)
$$I_D = -1 A$$
.

(4)
$$I_D = -2.3 A$$
.

(5)
$$I_D = -4.5 A$$
.

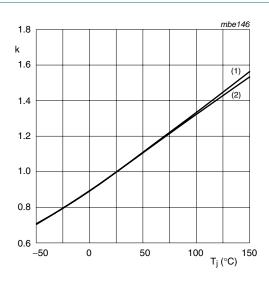


$$k = \frac{V_{GSth} \text{ at } T_j}{V_{GSth} \text{ at } 25^{\circ}C}$$

Typical V_{GSth} at I_D = 1 mA; V_{DS} = V_{GS} = V_{GSth} .







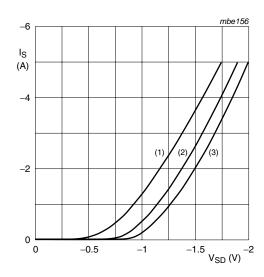
$$k = \frac{R_{DSon} \operatorname{at} T_{j}}{R_{DSon} \operatorname{at} 25^{\circ} C}$$

Typical R_{DSon} at:

(1)
$$I_D = -1 A$$
; $V_{GS} = -10 V$.

(2)
$$I_D = -0.5 \text{ A}$$
; $V_{GS} = -4.5 \text{ V}$.

Fig 10. Temperature coefficient of drain-source on-state resistance; P-channel



$$V_{GD} = 0V(1)T_j = 150^{\circ}C(2)T_j = 25^{\circ}C(3)T_j = -55^{\circ}C$$

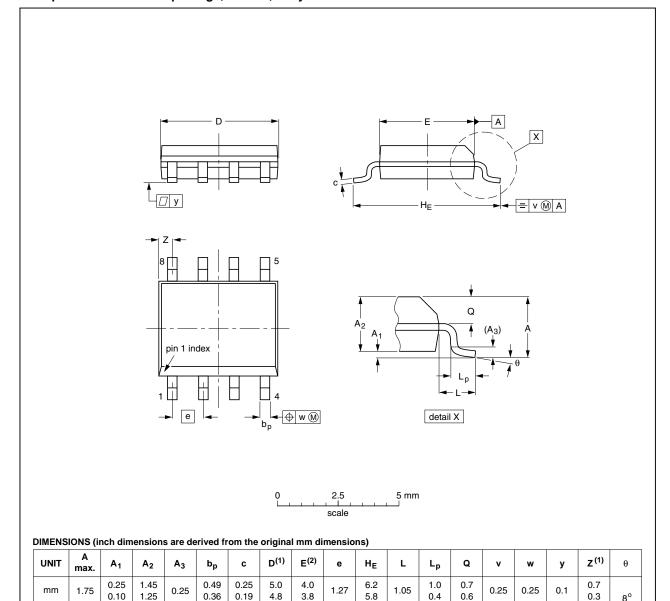
Fig 11. Source current as a function of source-drain voltage

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7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



Notes

inches

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.019 0.0100

0.014 0.0075

0.20

0.19

0.16

0.15

2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012			99-12-27 03-02-18

0.05

0.244

0.228

0.041

0.039

0.016

0.028

0.024

0.01

0.01

Fig 12. Package outline SOT96-1 (SO8)

0.010

0.004

0.069

0.057

0.049

0.01

PHP225

0°

0.028

0.004

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP225 v.4	20110317	Product data sheet	-	PHP225 v.3
Modifications:	 Various changes to 	content.		
PHP225 v.3	20110104	Product data sheet	-	PHP225 v.2

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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